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Application No.: 10/015,414

Docket No.: JCLA7737

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of :

Application No.

: 10/015,414

Filed

: December 12, 2001

For

: Method For Programming And Erasing Non-Volatile Memory With

Nitride Tunneling Layer

Applicant

: Tso-Hung Fan

Examiner

: Pham, Ly D

Art Unit

: 2818

PRELIMINARY AMENDMENT

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

The Advisory Office Action mailed December 8, 2003 has been carefully considered. In response thereto, please enter the following amendments for RCE and consider the following remarks.

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PAGE 3/7 * RGVD AT 12/27/2000 2:00:16 AM (Eastern Standard Time) * SVR:USPTO-EPIGE*-U0 * DNG9:9729390 * CSED:19496650809 * DARATION (mm-cs):01-42